

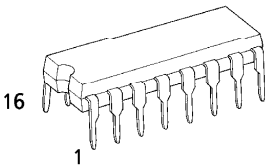
TC74HC133AP, TC74HC133AF

13-INPUT NAND GATE

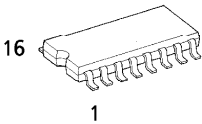
The TC74HC133A is a high speed CMOS 13-INPUT NAND GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 7 stages, including a buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 13\text{ns}$ (typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability..... 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4\text{mA}$ (Min.)
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range.... V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS133

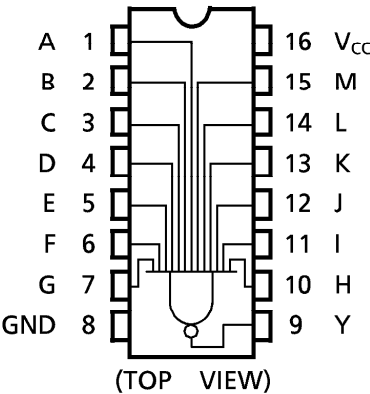


P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)

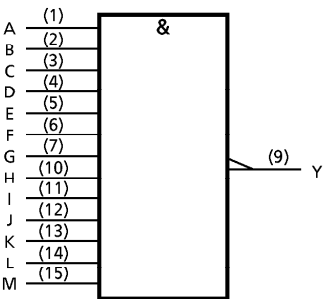


F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

Inputs	Output
All Inputs High	L
All Other Combinations	H

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2 \sim 6$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	t_r, t_f	$0 \sim 1000 (V_{CC} = 2.0\text{V})$ $0 \sim 500 (V_{CC} = 4.5\text{V})$ $0 \sim 400 (V_{CC} = 6.0\text{V})$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V
			4.5	3.15	—	—	3.15	—	
			6.0	4.20	—	—	4.20	—	
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V
			4.5	—	—	1.35	—	1.35	
			6.0	—	—	1.80	—	1.80	
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	V
			4.5	4.4	4.5	—	4.4	—	
		$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5	4.18	4.31	—	4.13	—	
			6.0	5.68	5.80	—	5.63	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	—	0.1	V
			4.5	—	0.0	0.1	—	0.1	
		$I_{OL} = 4 \text{ mA}$ $I_{OL} = 5.2 \text{ mA}$	4.5	—	0.17	0.26	—	0.33	
			6.0	—	0.18	0.26	—	0.33	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	1.0	—	10.0	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time	t_{PLH} t_{PHL}		—	13	22	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C				Ta = −40~85°C		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH} t _{THL}		2.0	—	25	75	—	95	ns
			4.5	—	7	15	—	19	
			6.0	—	6	13	—	16	
Propagation Delay Time	t _{pLH} t _{pHL}		2.0	—	42	130	—	165	ns
			4.5	—	16	26	—	33	
			6.0	—	14	22	—	28	
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Power Dissipation Capacitance	C _{PD} (1)			—	29	—	—	—	

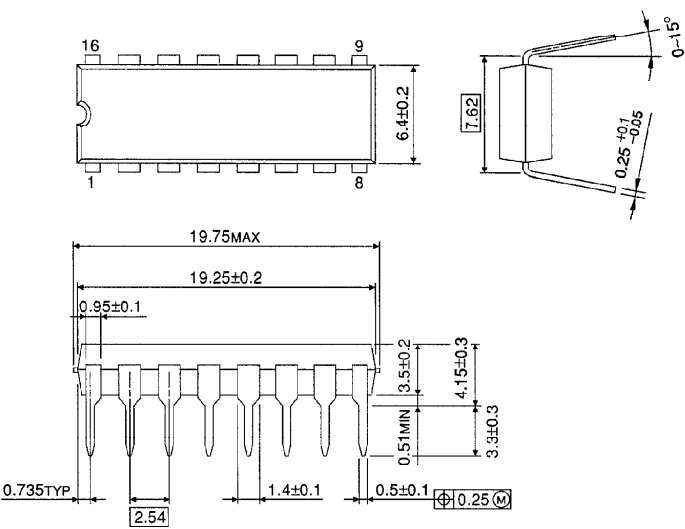
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

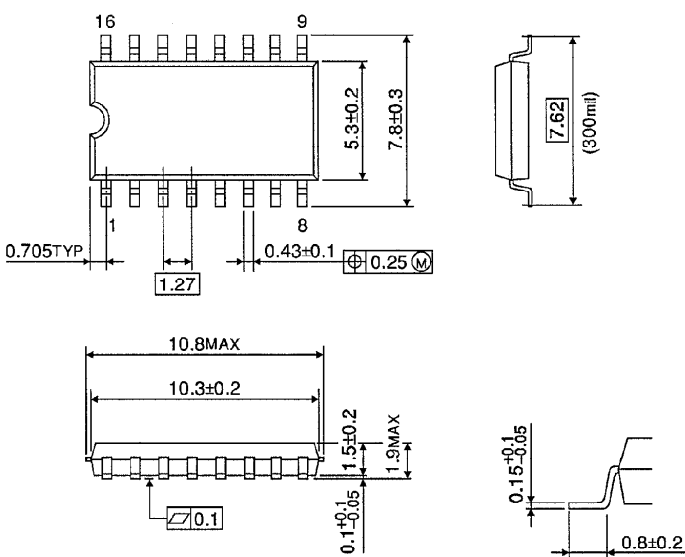
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)